

### **KSD1222**

# Power Amplifier Applications High DC Current Gain

- Low Collector-Emitter Saturation Voltage
- Built in a Damper Diode at E-C
- Darlington TR
- Complement to KSB907



### **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	3	А
I <sub>B</sub>	Base Current	0.3	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	15	W
	Collector Dissipation (T <sub>a</sub> =25°C)	1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 25 \text{mA}, I_B = 0$	40			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 60V, I_{E} = 0$			20	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			2.5	mA
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = 2V$ , $I_C = 1A$	2000			
$h_{FE2}$		$V_{CE} = 2V$ , $I_C = 3A$	1000			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_{C} = 2A, I_{B} = 4mA$			1.5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_{C} = 2A, I_{B} = 4mA$			2	V
t <sub>ON</sub>	Turn On Time	$V_{CC} = 30V, I_{C} = 3A$		0.1		μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = 6mA$		1		μs
t <sub>F</sub>	Fall Time	$R_L = 10\Omega$		0.2		μs

 $V_{CE} = 2V$ 

## **Typical Characteristics**

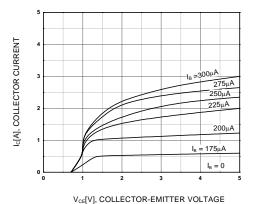


Figure 1. Static Characteristic

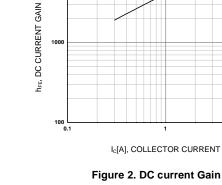


Figure 2. DC current Gain

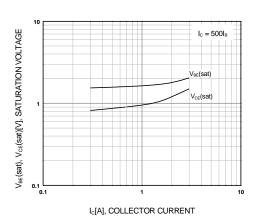


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

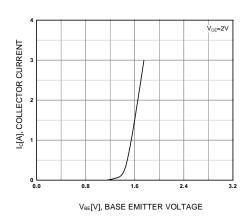


Figure 4. Base-Emitter On Voltage

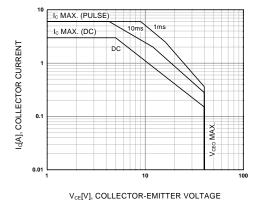


Figure 5. Safe Operating Area

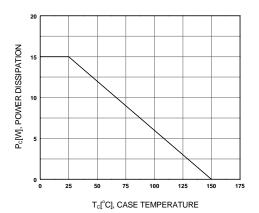
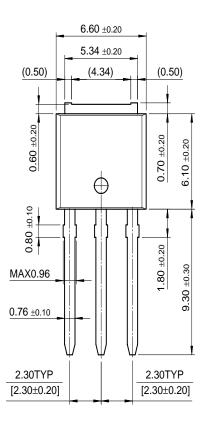


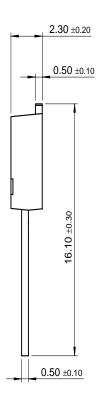
Figure 6. Power Derating

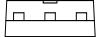
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## **Package Demensions**

## I-PAK







Dimensions in Millimeters

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Rev. H2

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